

isc Silicon NPN RF Transistor

DESCRIPTION

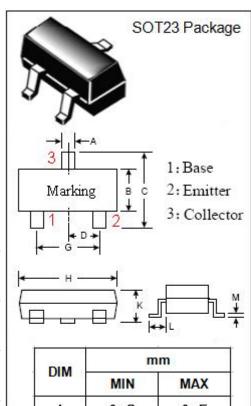
- · High Power Gain
- High Current Gain Bandwidth Product
- · Low Noise Figure
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for RF frontend in wideband applications in the GHz range, such as analog and digital cellular telephones, cordless telephones(CT1, CT2,DEC, etc.).

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	20	٧
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	2	V
Ic	Collector Current-Continuous	65	mA
Pc	Collector Power Dissipation @T _C =25°C	0.2	W
TJ	Junction Temperature	150	$^{\circ}$ C
T _{stg}	Storage Temperature Range	-65~150	$^{\circ}$ C



A	0.3 0.5			
В	1.2	1.4		
С	2. 25	2. 55		
D	0.	95		
G	1.8	2		
H	2.8	3		
K	0.9	1.15		
L.	0.	55		
M	0.08	0.15		

isc website: www.iscsemi.com

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BFR183

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; I _B = 0	12			V
Ісво	Collector Cutoff Current	V _{CB} = 10V; I _E = 0			0.1	uA
h _{FE}	DC Current Gain	I _C = 20mA ; V _{CE} = 6V	90		250	
f⊤	Current-Gain—Bandwidth Product	I _C = 20mA ; V _{CE} = 6V; f= 1GHz		8		GHz
C _{re}	Feedback Frequency	I _E = 0 ; V _{CB} = 10V; f= 1MHz		0.65		pF
S _{21e} ²	Insertion Power Gain	I _C = 20mA ; V _{CE} = 6V; f= 1GHz		12		dB
NF	Noise Figure	I _C = 5mA ; V _{CE} = 6V; f= 0.9GHz		1.6		dB

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